

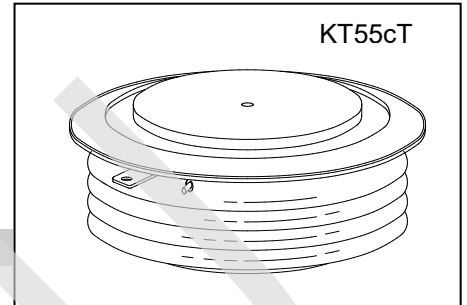


\*\*\*\*\*

### HIGH POWER THYRISTOR FOR PHASE CONTROL APPLICATIONS

#### Features:

- . All Diffused Structure
- . Amplifying Gate Configuration
- . Blocking capability up to 1800 volts
- . High  $dv/dt$  Capability
- . Pressure Assembled Device



### ELECTRICAL CHARACTERISTICS AND RATINGS

#### Blocking - Off State

Device Type	$V_{RRM}$ (1)	$V_{DRM}$ (1)	$V_{RSM}$ (1)
KP1200/12	1200	1200	1400
KP1200/14	1400	1400	1600
KP1200/16	1600	1600	1800
KP1200/18	1800	1800	2000

$V_{RRM}$  = Repetitive peak reverse voltage  
 $V_{DRM}$  = Repetitive peak off state voltage  
 $V_{RSM}$  = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	$I_{RRM}/I_{DRM}$	5 mA 80 mA (3)
Critical rate of voltage rise	$dv/dt$ (4)	1000 V/ $\mu$ sec

#### Notes:

- (1) All voltage ratings are specified for an applied 50Hz/60Hz sinusoidal waveform over the temperature range 0 to +125 °C.
- (2) 10 msec. max. pulse width
- (3) Maximum value for  $T_j = 125$  °C.
- (4) Minimum value for linear and exponential waveshape to 67% rated  $V_{DRM}$ . Gate open.  $T_j = 125$  °C.
- (5) The value of  $di/dt$  is established in accordance with standard JB/T 8950.2-2013

#### Conducting - On State

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Average value of on-state current	$I_{T(AV)}$		1200		A	Sinewave, 180° conduction, $T_c = 70$ °C
RMS value of on-state current	$I_{TRMS}$		1884		A	Nominal value
Peak one cycle surge (non repetitive) current	$I_{TSM}$		14400		A	10.0 msec (50Hz), sinusoidal wave-shape, 180° conduction, $T_j = 125$ °C
I square t	$I^2t$		$10 \times 10^5$		A <sup>2</sup> s	10 msec
Latching current	$I_L$		1000		mA	$V_D = 12$ V; $R_L = 12$ ohms
Holding current	$I_H$		200		mA	$V_D = 12$ V; $I = 2.5$ A
Peak on-state voltage	$V_{TM}$		1.60		V	$I_{TM} = 3000$ A; $T_j = 25$ °C
Threshold voltage, low-level	$V_{TO}$		0.88		V	$T_j = 125$ °C
Slope resistance, low-level	$r_T$		0.2		m $\Omega$	1000A to 3000A
Critical rate of rise of on-state current	$di/dt$		200		A/ $\mu$ s	Repetition

**Gating**

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Peak gate power dissipation	$P_{GM}$		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	$I_{GT}$		200		mA	$V_D = 12\text{ V}; R_L = 3\text{ ohms}; T_j = +25\text{ }^\circ\text{C}$
Gate- trigger voltage	$V_{GT}$	0.70	2.5		V	$V_D = 12\text{ V}; R_L = 3\text{ ohms}; T_j = +25\text{ }^\circ\text{C}$
Peak negative voltage	$V_{GRM}$		5		V	

**Dynamic**

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Delay time	$t_d$		3.0	2.5	$\mu\text{s}$	$I_{TM} = 100\text{ A}; V_D = 67\% V_{DRM}$ Gate pulse: $V_G = 30\text{ V}; R_G = 10\text{ ohms};$ $t_r = 0.1\mu\text{s}; t_p = 20\mu\text{s}$
Turn-off time (with $V_R = -5\text{ V}$ )	$t_q$			250	$\mu\text{s}$	$I_{TM} = 1000\text{ A}; di/dt = -10\text{ A}/\mu\text{s};$ $V_R = 50\text{ V}; dV/dt = 30\text{ V}/\mu\text{s};$ $V_D = 67\% V_{DRM}; T_j = 125\text{ }^\circ\text{C}$
Reverse recovery charge	$Q_{rr}$			2000	$\mu\text{C}$	$I_{TM} = 1000\text{ A}; di/dt = -10\text{ A}/\text{s};$ $V_R = 50\text{ V}; T_j = 125\text{ }^\circ\text{C}$

**THERMAL AND MECHANICAL CHARACTERISTICS AND RATINGS**

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Operating temperature	$T_j$	-40	+125		$^\circ\text{C}$	
Storage temperature	$T_{stg}$	-40	+140		$^\circ\text{C}$	
Thermal resistance - junction to case	$R_{\Theta(j-c)}$		0.022		$^\circ\text{C}/\text{W}$	Double sided cooled
Thermal resistance - case to heatsink	$R_{\Theta(c-s)}$		0.005		$^\circ\text{C}/\text{W}$	Double sided cooled
Mounting force	P	22	27	25	kN	
Weight	W			0.46	kg	

\* Mounting surfaces smooth, flat and greased

